













ESD

TVS

TSS

MOV

GDT

PLED

MSB20B THRU MSB20M

Product specification





MSB20B THRU MSB20M

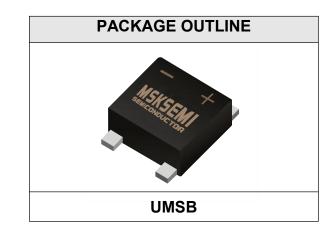
VOLTAGE RANGE 1000 Volts CURRENT 2.0 Ampere

Features

- Glass Passivated Chip Junction
- Reverse Voltage 100 to 1000 V
- Forward Current 2.0 A
- High Surge Current Capability
- Designed for Surface Mount Application

MECHANICAL DATA

- Case: UMSB
- Terminals: Solderable per MIL-STD-750, Method 2026



Maximum Ratings and Electrical characteristics

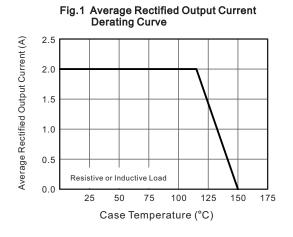
Ratings at $25\,^\circ$ C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	MODOCT	MODOCT	MODOOO	MODOCI	MODOCH	MODOON	Unite
Parameter	Symbols	MSB20B	MSB20D	MSB20G	MSB20J	MSB20K	MSB20M	Units
Maximum Repetitive Peak Reverse Voltage	Vrrm	100	200	400	600	800	1000	V
Maximum RMS voltage	V RMS	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	Vdc	100	200	400	600	800	1000	V
Average Rectified Output Current	lo	2.0					A	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	Ifsm	50					A	
Maximum Forward Voltage at 2.0 A	VF	1.1					V	
Maximum DC Reverse Current $@TA=25^{\circ}$ at Rated DC Blocking Voltage $@TA=125^{\circ}$	I _R	5 100					μA	
Typical Junction Capacitance (Note1)	Cj	30					рF	
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150				°C		

Note: 1. Measured at 1MHz and applied reverse voltage of 4 V D.C.

2. Mounted on glass epoxy PC board with 4×1.5 " $\times 1.5$ " (3.81×3.81 cm) copper pad.





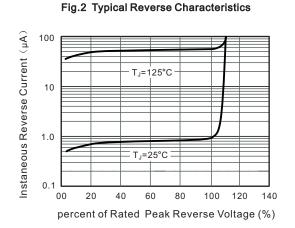


Fig.4 Typical Junction Capacitance

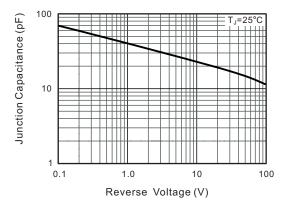


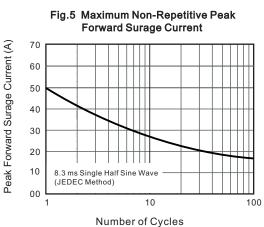
Fig.3 Typical Instaneous Forward Characteristics Instaneous Forward Current (A) 10 TJ=25°C 1.0 0.1 pulse with 300µs 1% duty cycle 0.01

1.0

Instaneous Forward Voltage (V)

1.5

2.0



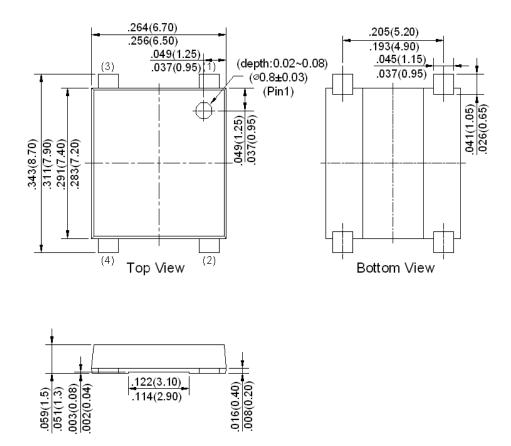
0.5

0.0

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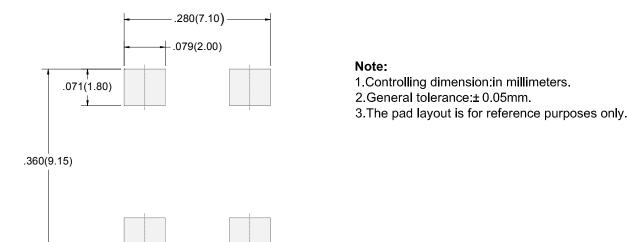


UMSB Package Outline Dimensions



Dimensions in inches and (millimeters)

UMSB Suggested Pad Layout



REEL SPECIFICATION

P/N	PKG	QTY
MSB20B THRU MSB20M	UMSB	3000



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